Evidence for a quantum phase transition in electron-doped $Pr_2 _xCe_xCuO_4$ from therm opower m easurem ents

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The evidence for a quantum phase transition under the superconducting dome in the high- T_c cuprates has been controversial. We report low temperature norm al state therm opower(S) measurements in electron-doped Pr₂ x Ce_xCuO₄ as a function of doping (x from 0.11 to 0.19). We nd that at 2 K both S and S/T increase dram atically from x=0.11 to 0.16 and then saturate in the overdoped region. This behavior has a remarkable similarity to previous Halle ect results in Pr₂ x Ce_xCuO₄ . Our results are further evidence for an antiferrom agnetic to param agnetic quantum phase transition in electron-doped cuprates near x=0.16.

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The existence of a quantum phase transition at a doping under the superconducting dom e in high-T_c superconductors is still controversial. E vidence for a quantum critical point has been given for hole-doped cuprates^{1,2,3} but the T=0 normal state is di cult to access because of the large critical eld (H_{c2}). Electron-doped cuprates have a relatively low H_{c2} and several studies have suggested that a quantum phase transition exists in those cuprates. Electrical transport⁴ on electron-doped $Pr_{2x} Ce_{x}CuO_{4}$ (PCCO) shows a dramatic change of Hall coe cient around doping $x_c = 0.16$, which indicates a Ferm i surface rearrangem ent at this critical doping. Optical conductivity experiments⁵ revealed that a densitywave-like gap exists at nite tem peratures below the critical doping x_c and vanishes when x x_c. Neutron scattering experiments⁶ on N d_{2 x} C e_x C uO ₄ (N C C O) found antiferrom agnetism as the ground state below the critical doping while no long range m agnetic order was observed above x_c . O ther suggestive evidence' com es from the observation of a low temperature norm al state insulator to metal crossover as a function of doping, and the disappearance of negative spin m agnetoresistance at a critical doping⁸. All these experiments strongly suggest that an antiferrom agnetic (AFM) to param agnetic quantum phase transition (QPT) occurs under the superconducting dom e in the electron-doped cuprates.

The quantum phase transition in electron-doped cuprates is believed to be associated with a spin density wave (SDW) induced Ferm isurface reconstruction^{5,9}. Angle resolved photoem ission spectroscopy (ARPES) experiments¹⁰ on NCCO reveal a small electron-like pocket at(;0) in the underdoped region and both electron- and hole-like Ferm i pockets near optim al doping. This interesting feature is thought to arise as a result of the SDW instability that fractures the conduction band into two di erent parts³. If one continues to increase the doping (above x_c), the weakening of the spin density wave leads to a large hole-like Ferm i pocket centered at (;) in the overdoped region^{9,11}.

Nevertheless, the presence of a quantum critical point (Q C P) under the superconducting dome in electrondoped cuprates is still quite controversial¹². O there experim ental probes of the critical region are needed. In this paper, we present a system atic study of the magnetic

eld driven norm al state therm opower on PCCO Im s. We nd a doping dependence sim ilar to that seen in the low tem perature norm al state H alle ect m easurem ent⁴. From a simple free electron m odel com parison of these two quantities, we nd a strikingly sim ilar behavior of the e ective number of carriers. This strongly suggests that a quantum phase transition takes place near x = 0.16in PCCO.

High quality PCCO In swith thickness about 3000A were fabricated by pulsed laser deposition on SrT iO₃ substrates (10 5 mm²). Detailed information can be found in our previous papers^{13,14}. The Im swere characterized by AC susceptibility, resistivity measurements and Rutherford Back Scattering (RBS).

High resolution therm opower is measured using a steady state m ethod by switching the tem perature gradient to cancel the Nemste ect and other possible background contributions. The sam ple is mounted between two therm ally insulated copper blocks. The tem perature gradient is built up by applying power to heaters on each block and the gradient direction is switched by turning on or o the heaters. The tem perature gradient is monitored by two Lakeshore Cernox bare chip therm om eters. Therm opower data is taken when the gradient is stable and averaged for many times to reduce the system atic error. The voltage leads are phosphor bronze, which has a small therm opower even at high eld^{15} . The therm opower contribution from the wire is calibrated against $YBa_2Cu_3O_7$ ($T_c = 92K$) for T < 90K and Pb lm for T > 90K, and is subtracted out to get the absolute therm opower of the PCCO sample.

We measured the zero eld and in eld resistivity of

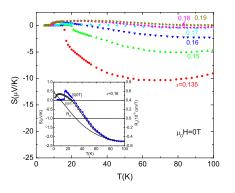


FIG. 1: (Color online) Them opower S versus temperature (T < 100 K) at zero eld for all the superconducting PCCO lm s. Inset is the therm opower S of x=0.16 lm at zero eld (solid blue circle) and $_0H=9$ T (open circle) as a function of temperature. Solid line is the temperature dependence of the Hall coe cient for the same lm.

all the doped PCCO Im s. The results are similar to our previous report⁴. A 9 T m agnetic eld (H kc) is enough to suppress the superconductivity for all the dopings. This enables us to investigate the low temperature norm al state properties in PCCO. A low temperature resistivity uptum is seen for doping below x=0.16, which suggests a possible insulator to m etal crossover as a function of doping⁷.

Therm opower is measured on the PCCO $\,$ In s doped from x=0.11 to 0.19. In zero ekl, a sharp superconducting transition is clearly seen in the therm opower. In the inset of Fig. 1, we show the therm opower S of x=0.16 (T_c=16.5 K) as a function of tem perature. Our high resolution therm opower setup enables us to observe small changes of signal. When the sam ple goes to the superconducting state, S=0, a small change 4 S=0.5 V/K is easily detectable, which indicates a better sensitivity than our previous one-heater-two-therm om eter setup^{16}. We also show the H allcoe cient $R_{\rm H}$ as a function of tem – perature for the sam e $\,$ Im in the graph. A sign change of both S and $R_{\rm H}$ is observed at the sam e tem perature.

In the main panel of Fig. 1, we show the zero eld them opower for all the superconducting lm s. A clear superconducting transition is seen in these lm s. The norm al state S (T > T_c) is negative in the underdoped region. It becomes positive in the overdoped region at low tem perature (to be shown later). The magnitude of S in the underdoped region is large as expected for a system with less charge carrier density while it is much smaller in the overdoped region. Previous zero eld them opower measurem ents on NCCO crystals¹⁷ are qualitatively sim – ilar to our data.

W hen a 9 T magnetic eld is applied along the caxis, the superconducting lm s are driven to the normal state for $T < T_c$. As seen from the inset of Fig. 1,

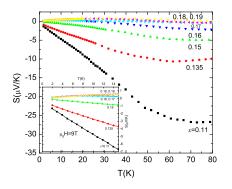


FIG. 2: (Color online)The normal state them opower S($_0H = 9 T > _0H_{c2}$) of all the doped lms versus tem perature. Inset shows the low tem perature (T < 15 K) data.

when the superconductivity is destroyed, the norm al state therm opower is obtained. In Fig. 2, we show the norm al state therm opower for all the lms. The low tem perature (T < 15 K) norm all state therm opower is shown in the inset. We showed in Fig. 1 that for x=0.16 the therm opower changes from negative to posit ive for T < 30 K, in good agreem ent with the Hall effect m easurem ents⁴. For the overdoped $\ln s x = 0.17$ and 0.18, we observe similar behavior with a sign change occurring below 45 K and 60 K respectively. However, the therm opower is always positive for x = 0.19. Sim ilar to the the Halle ect, the therm opower for x 0.16 is nearly same for T < 10 K, as shown in the inset of Fig. 2. The dram atic change of the therm opower at low tem perature from x = 0.15 to the overdoped region suggests a sudden Ferm i surface rearrangem ent around the critical doping x = 0.16.

In the Boltzm ann picture, them opower and electrical conductivity are related through the expression¹⁸:

$$S = \frac{{}^{2}k_{B}^{2}T}{3e}\frac{\partial \ln ()}{\partial j_{E_{F}}} j_{E_{F}}$$
(1)

In the simple case of a free electron gas, this yields: S=T = $\frac{2k_B^2}{3e} \frac{N(F)}{n}$ (N(F) is the density of states at the Fermi energy and n is the total number of charge carriers). However, in real metals, the energydependence of the scattering time at the Ferm i level, $\left(\frac{\theta \ln (1)}{2}\right) = \frac{1}{2}$, also a ects the therm opower. In the zerotem perature lim it, it has been shown that this term also becomes proportional to $\frac{N(F)}{n}$ when the impurity scattering dom inates¹⁹. In electron-doped cuprates, there is strong evidence⁴ for impurity scattering at low temperatures. The residual resistivity is about 50 -cm for an optimally-doped lm, which is quite large compared to clean m etals, and the tem perature dependence of the resistivity becom es alm ost constant below 20 K. This is all suggestive of strong in purity scattering. The scattering most likely comes from Ce and oxygen disorder and one

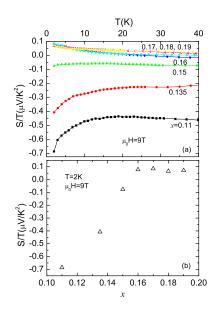


FIG.3: (Color online) (a) S/T versus tem perature (T < 40 K and $_0\text{H} = 9 \text{ T}$) for all the lm s. (b) S/T (T = 2 K and $_0\text{H} = 9 \text{ T}$) as a function of doping x.

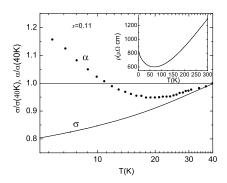


FIG. 4: Normalized = S=T and (T) for x=0.11 versus temperature for T 40 K. Inset shows the temperature dependence of in plane resistivity (T) for the same lm.

would expect a similar disorder at all dopings, although this is hidden by the anom alous (and unexplained) resistivity uptum for the lower dopings. Therefore, we expect that the therm opower is proportional to N (E_F)/n will be a valid approximation for our electron-doped PCCO

In s. This theory thus provides a solid theoretical basis for an experim ental observation: in a wide variety of correlated m etals, there is an experim ental correlation between the magnitude of therm opower and speci c heat in the zero-tem perature lim it^{20} .

Let us exam ine our data with this picture in m ind. Fig. 3(a) presents S/T as a function of tem perature below 40 K for all the doped lm s. As seen in the gure, there is a dram atic di erence between the underdoped and the overdoped Im s. For underdoped, S/T displays a strong tem perature dependence below 20 K, which is rem iniscent of the low temperature upturn in resistivity and Halle ect^{4} . One possible explanation for this feature would be charge localization²¹. If all, or some of, the itinerant carriers localize at very low temperatures, then the decrease in conductivity is expected to be concom itant with an increase in the entropy per itinerant carrier (which is the quantity roughly measured by S/T).We nd this to be qualitatively true as shown in Fig. 4, which displays S/T and conductivity for x = 0.11in a sem ilog plot. Below 10 K, both quantities are linear functions of logT . Note that for the resistivity, it has been show n⁷ that the logarithm ic divergence saturates below 1 K. Therefore, further therm opower measurements below 2 K would be very useful.

In contrast to the underdoped lm s, the tem perature dependence of S/T in the overdoped region is weaker and there is clearly a nite S/T even at zero tem perature. Taking the magnitude of S/T at 2 K as our reference, we can exam ine the doping dependence of the ratio $\frac{N(p)}{n}$ for itinerant carriers at this tem perature. F ig. 3 (b) presents the doping dependence of S/T at 2 K. A strong doping dependence for x 0.16, a sharp kink around x= 0.16 and a saturation in the overdoped region are visible. The dram atic change of S/T at low tem peratures from the underdoped to overdoped regions is sim ilar to the H all e ect⁴ at 0.35 K, in which a sharp kink was observed around x= 0.16. B oth S/T and R_H change from negative in the underdoped region to a saturated positive value above x= 0.16.

The similarity of the doping dependence of S/T and $R_{\rm H}$ implies a common physical origin. To explore the relation between S/T and $R_{\rm H}$, let us assume a simple free electron model, where therm opower displays a very simple correlation with the electronic speci c heat, $C_{\rm el} = \frac{\frac{2}{R_{\rm H}^2}T}{3}N$ ($_{\rm F}$). Following the analysis of Ref20, a dimensionless quantity

$$q = \frac{S}{T} \frac{N_{Av}e}{}$$
(2)

can be de ned (N_{A_V}) is Avogadro's number and = $C_{el}=T$), which is equal to $N_{A_V}=n$. For a simple metal, $R_H = V=ne$ (V is the total volume). If we de ne

$$q^0 = R_H e V_m$$
(3)

where V_m is unit cell volume, then q^0 is also equal to $N_{Av}=n$. By this simple argument, we can compare S and R_H directly. Because we do not have data for except at optim al doping, we assume it does not change much with doping. With the value(4m J=K²m ole)²² for x= 0.15 and S/T and R_H at 2 K, we can plot both q and q^0 together, as shown in Fig. 5. We ind a remarkable similarity in the doping dependence of these two dimensionless quantities, both in trend and in magnitude. Note that no dramatic changes in either q or q^0 are observed near x= 0.13, where it is claimed that

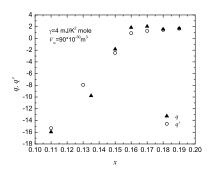


FIG. 5: Doping dependence of q(2 K) and q'(2 K) of PCCO Im s(q and q' are de ned by Eq. (2) and (3) in the text).

A FM long range order vanishes¹² from recent neutron scattering m easurements. We should mention that assuming a constant as a function of doping in our range of investigation (x=0.11 to 0.19) is, of course, subject to caution due to a lack of experimental data. However, it has been found²² that the speci c heat coe cient is the same for an as-grown crystal and a superconducting P $r_{1:85}C e_{0:15}C uO_4$ crystal. Neutron scattering studies have shown that an as-grown x=0.15 crystal is equivalent to an annealed P $r_{1:85}C e_{0:12}C uO_4$ crystal²³. This strongly suggests that will not change m uch with Ce doping at least in the critical range around optim aldoping. Therefore, no signi cant change in the doping dependence of q due to this correction is expected.

W e believe that the saturation of S/T in the overdoped region is a result of the Ferm i surface rearrangement due to the vanishing of antiferrom agnetism above a critical doping. To our know ledge, there is no theoretical prediction for the doping dependence of the therm opower in an antiferrom agnetic quantum critical system . A though the tem perature dependence of therm opower near zero tem perature is given by Paul et al.²⁴ for such a system near critical doping, we are not yet able to access the very low tem perature region (T < 2 K) to test these predictions in PCCO. Nevertheless, an am azing agreem ent between therm opower and Hall e ect measurements is shown in our simple free electron model. This model is certainly oversimpli ed since there is strong evidence for two types of carriers near optim al doping^{25,26,27}. But, m uch of this transport data^{25,26,27} im plies that one type of carrier dom inates at low tem perature. Thus a simple m odelm ay be reasonable. How ever, to better understand this striking result a more detailed theoretical analysis will be needed.

Interestingly, the number q in overdoped PCCO is close to 1. It was shown that when q is close to unity, a Ferm i liquid behavior is found in many strongly correlated materials²⁰. This suggests that overdoped PCCO is more like a Ferm i liquid metal than underdoped PCCO. When x is above the critical doping x=0.16, q and q⁰ are close to 1=(1 x), which suggests that the hole-like Ferm i surface is recovered in accordance with local density approximation band calculations and the Luttinger theorem .

In summary, we performed high resolution measurements to investigate the low temperature normal state therm opower(S) of electron-doped cuprates $Pr_{2 \ x} Ce_{x}CuO_{4}$ (PCCO).We nd a strong correlation between S/T and the Hall coe cient ($R_{\rm H}$) at 2 K as a function of doping. Using a simple free electron model, which relates therm opower to the electronic speci cheat, we conclude that our observations support the view that a quantum phase transition occurs near x=0.16 in the PCCO system.

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- ¹ Y.Ando et al, Phys.Rev.Lett.92, 247004 (2004) and references therein.
- ² J.L.Tallon and J.W .Loram Physica C 349,53 (2001).
- ³ G Q. Zheng et al, Phys. Rev. Lett. 94, 047006 (2005).
- ⁴ Y.Dagan et al, Phys. Rev. Lett. 92, 167001 (2004).
- ⁵ A.Zimmersetal, Europhys. Lett. 70, 225 (2005).
- ⁶ H.Kang et al., Nature (London) 423, 522 (2003).
- ⁷ P.Foumier et al, Phys. Rev. Lett.81, 4720 (1998).
- ⁸ Y.D agan et al, Phys. Rev. Lett.94, 057005 (2005).
- ⁹ J.Lin and A.J.M illis, Phys.Rev.B 72, 214506 (2005).
- ¹⁰ N.P.A.m itage,et al,Phys.Rev.Lett. 88, 257001 (2002).
 ¹¹ H.M atsui et al,Phys.Rev.Lett. 94, 047005 (2005); H.
 M atsui, et al, Phys.Rev.Lett. 95, 017003 (2005).
- ¹² Recent neutron scattering experiments on N d_{2 x} C e_x C uO $_4$ argue that the QCP is at x=0.13 and that the superconductivity and AFM do not coexist, E M .M otoyam a et al., cond-m at/0609386.
- ¹³ J.L.Peng et al, Phys.Rev.B 55 R 6145 (1997).

- $^{14}\,$ E .M aiser et al,P hysica (A m sterdam) 297C , 15(1998).
- ¹⁵ Y.W ang et al., Nature (London) 423, 425 (2003).
- ¹⁶ R.C.Budhanietal, Phys.Rev.B 65, 100517(R) (2002).
- ¹⁷ C.H.W ang et al, Phys.Rev.B 72,132506 (2005).
- ¹⁸ N.W. A shcroft and N.D. Mermin, Solid State Physics, Saunders College Publishing (1976).
- ¹⁹ K. M iyake and H. Kohno, J. Phys. Soc. Jpn, 74, 254 (2005).
- ²⁰ K.Behnia, D.Jaccard and J.Flouquet, J.Phys.Condens. M atter 16, 5187 (2004).
- ²¹ P.Fournier et al, Phys.Rev.B 62, R11993 (2000).
- ²² H.Balci and R.L.Greene, Phys. Rev. B 70 140508 (R) (2004).
- ²³ P.K.M ang et al, Phys.Rev.Lett. 93, 027002 (2004).
- ²⁴ I.Pauland G.Kotliar, Phys. Rev. B 64, 184414 (2001).
- ²⁵ W .Jiang et al, Phys. Rev. Lett. 73, 1291 (1994).
- ²⁶ P.Fournier et al, Phys.Rev.B 56, 14149(1997).
- ²⁷ F.Gollnik and M.Naito, Phys.Rev.B 58, 11734(1998).